

The Properties of Cryogenic CMOS Avalanche Photodiodes

SSPM Detector for Polarized Target Scintillator Readout

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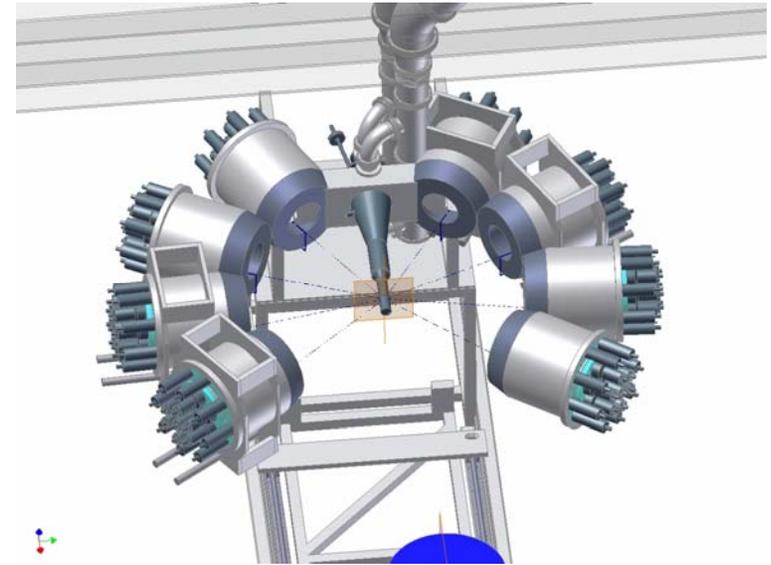
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Extreme Environments and the Polarizability of Protons

- **Goal: Develop photodetectors with gain that operate in extreme environments:**
 - Temperatures around a few Kelvin
 - High magnetic fields of several Tesla
 - High-helium environments.
 - Small physical spaces of less than 1 cm x 1 cm
- **PMTs will fail if exposed to these types of environments, where a solid-state photodetector may not.**
- **New class of nuclear physics experiments:**
 - Look at spin polarizability of nucleons
 - Spin polarizabilities characterize how circularly polarized photons interact with a polarized nucleon.
 - Little is known how circularly polarized fields influence polarized protons.
- **Scatter circularly polarized photons off of polarized protons.**
- **HIFROST:**
 - Polarized proton target
 - NaI detectors are used to measure scattering kinematics
 - Few Tesla
 - Target at a few milliKelvin

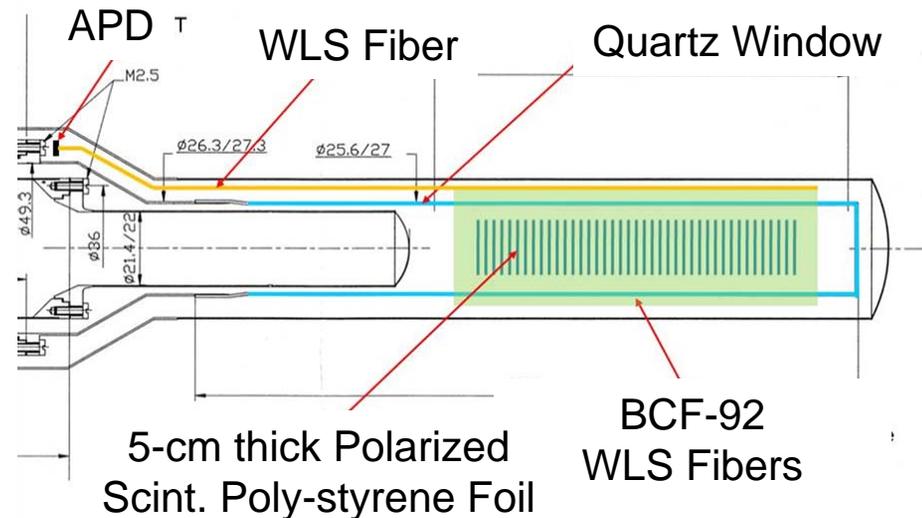


➤ Background Rejection

- Target is a hydrocarbon scintillator with embedded polarized protons
- Rejection of backgrounds is done using a coincidence signal
 - NaI signal
 - Scintillator signal
 - Beam signal
- Scintillator will be readout with a photodetector

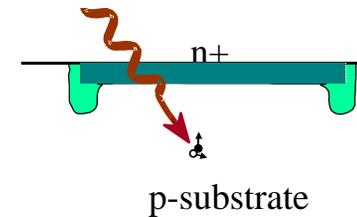
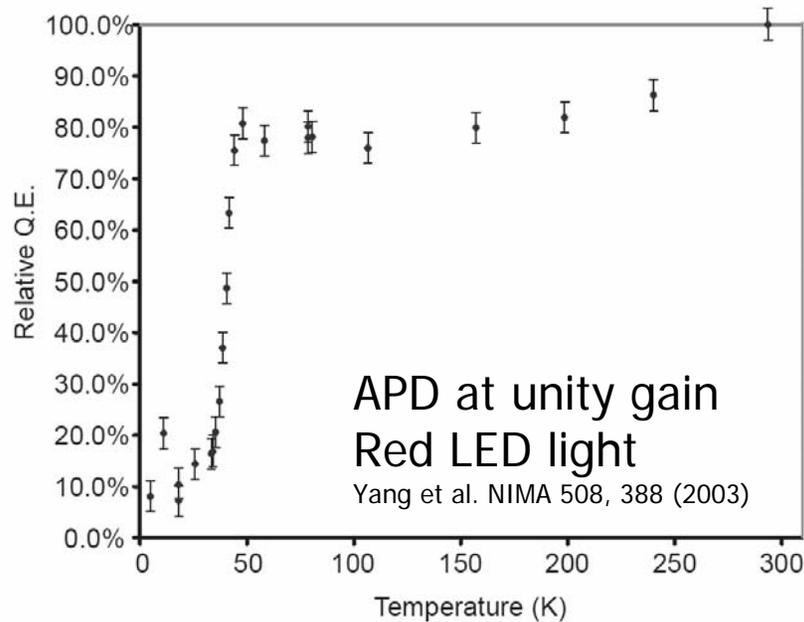
Polarized Proton Target

Light capture with wavelength shifters



- A PMT can not be used for the existing target cryostat: A complete redesign of the system would be required.
- Mount photodetectors outside the dilution refrigerator: Temperature ~ 3-4 K
- Scintillation rests within a transparent vessel
- Wave-length shifting fibers (Saint Gobain BCF-92, max. emission 480nm) are use to collect the light and transport it to the photodetector.
- The design goal is to obtain photon collection efficiencies of approximately 10% with an energy resolution of 10%.
- This resolution is necessary to reject backscattered protons freed from ^{12}C atoms in comparison to the scatter of free polarized protons.

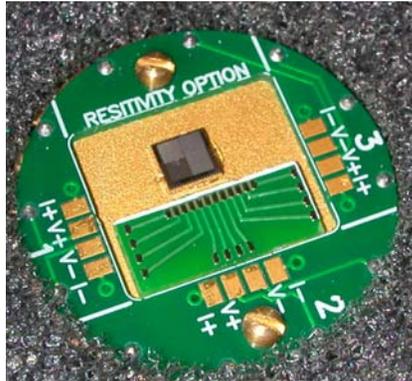
GPD Operation at Low Temperatures



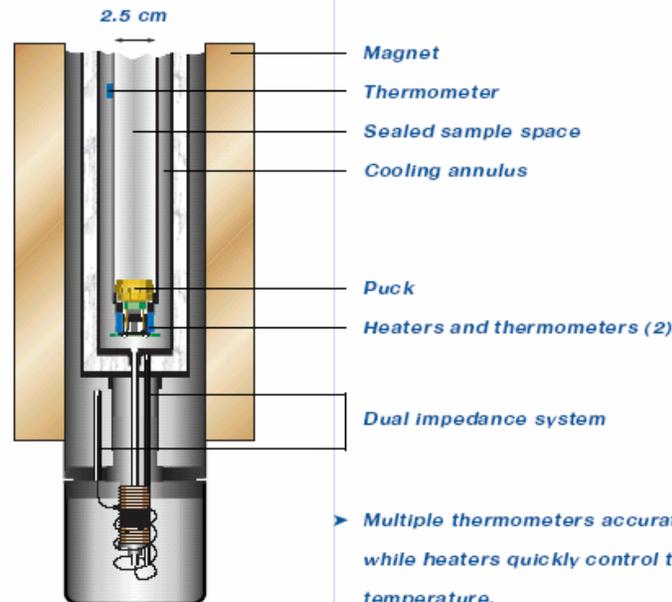
- Typical APD structure is doped to reduce excess noise at room temperature.
- Large gains are achieved at high biases (~1000 V).
- Carrier loss is a viable explanation for loss of QE below 40 K.

- Geiger Photodiode (GPD) is an avalanche photodiode operated beyond the breakdown voltage.
- The GPD is the basic building block for a solid-state photomultiplier.
- Doping leads to a low voltage breakdown.
- Carrier loss should be less of an issue.

Setup for GPD Evaluation

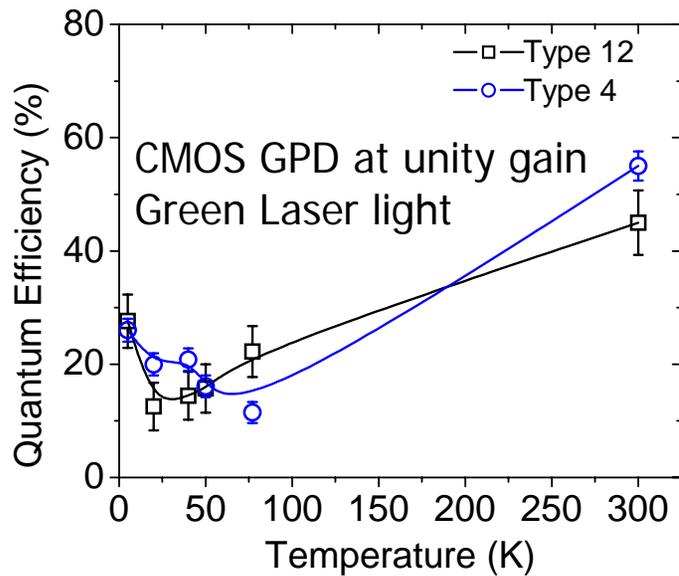
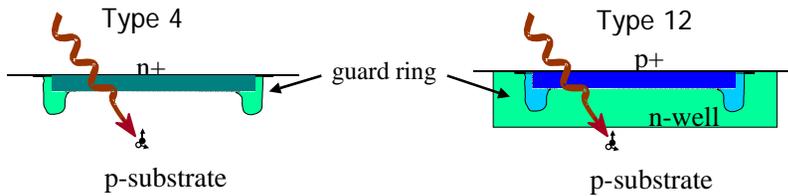


Puck with
SSPM and GPD

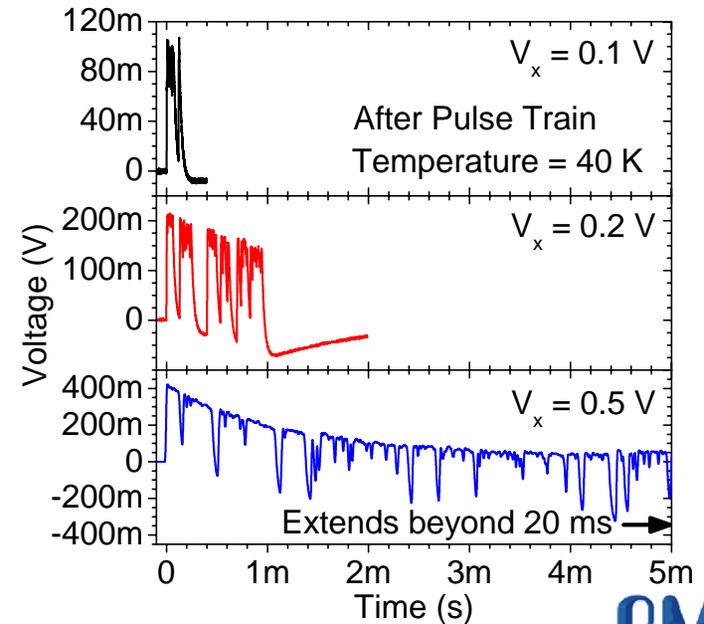
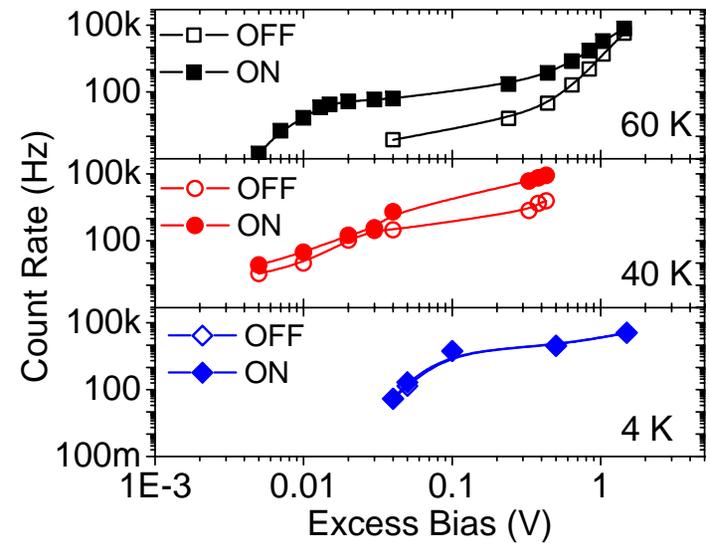


- Mounted GPD and SSPM to puck for insertion into cryostat at the University of Massachusetts.
- Mounted LED and Laser to a viewport on the cryostat to inject light into the system.

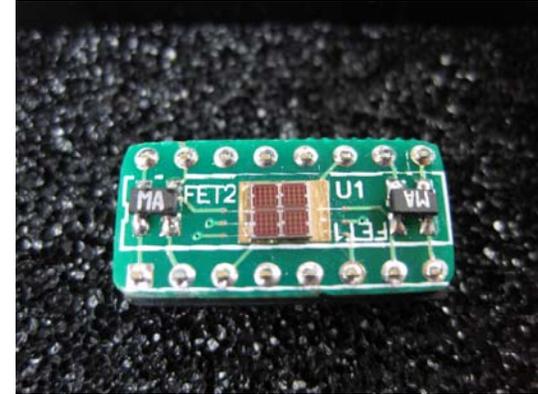
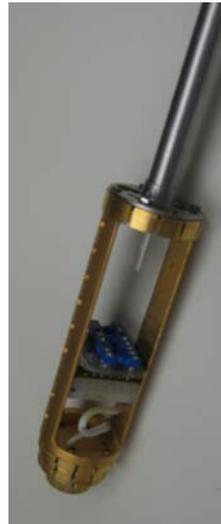
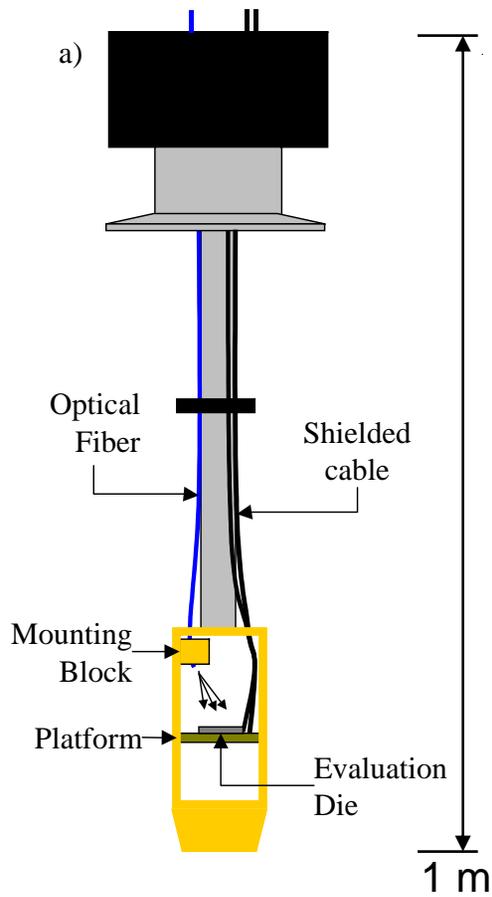
GPD Results



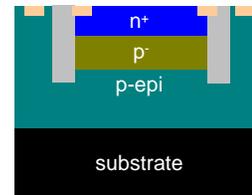
- Excess noise at low temperatures.
- After pulsing effect.



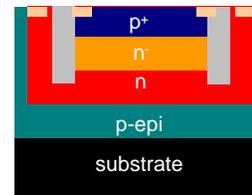
APD Setup



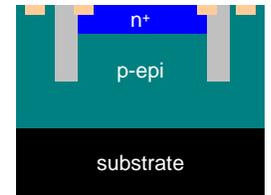
Type 7



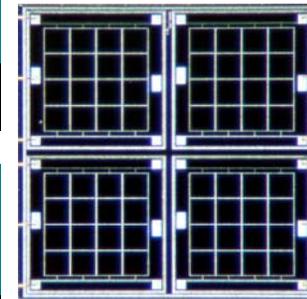
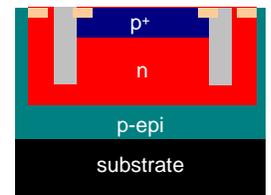
Type 14



Type 4

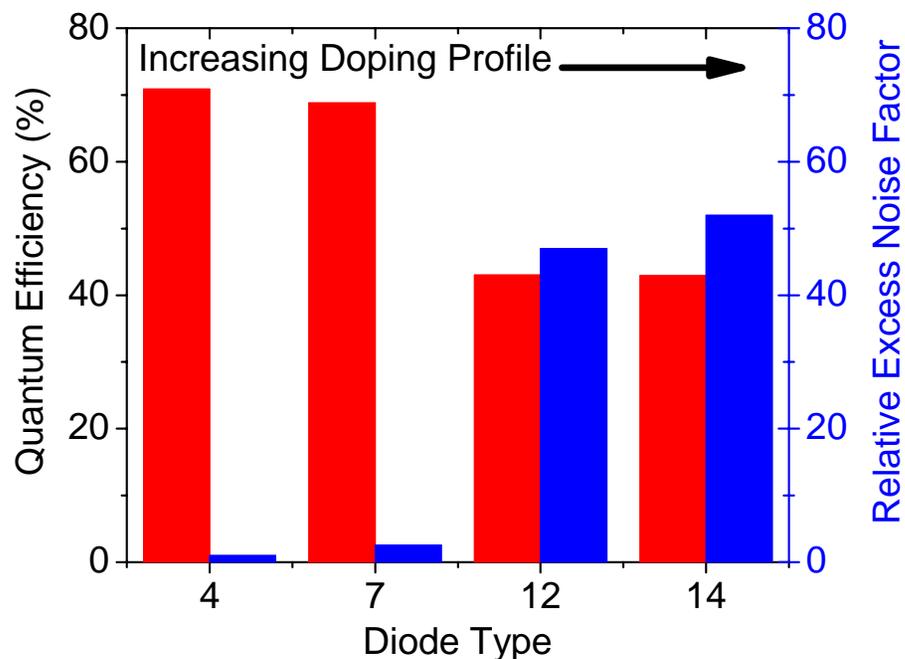
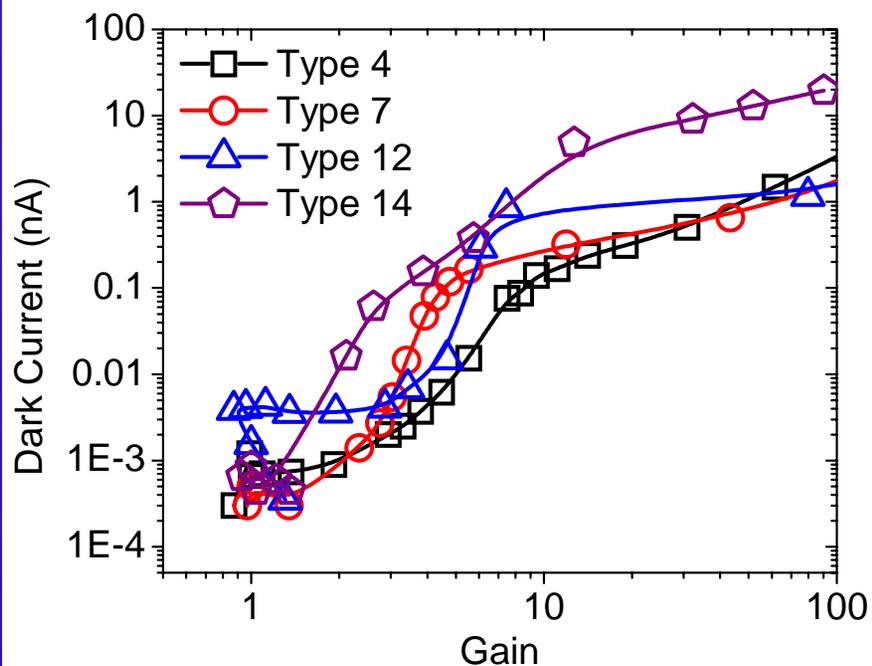


Type 12



Determining Best Diode

- Determine the QE, gain, dark noise and excess noise at 4 Kelvin.



- QE and Gain measured with a 532 nm LED.
- Excess noise is determined by pulsing the LED to collect a pulse height distribution.
- Best Diode: Type 4.

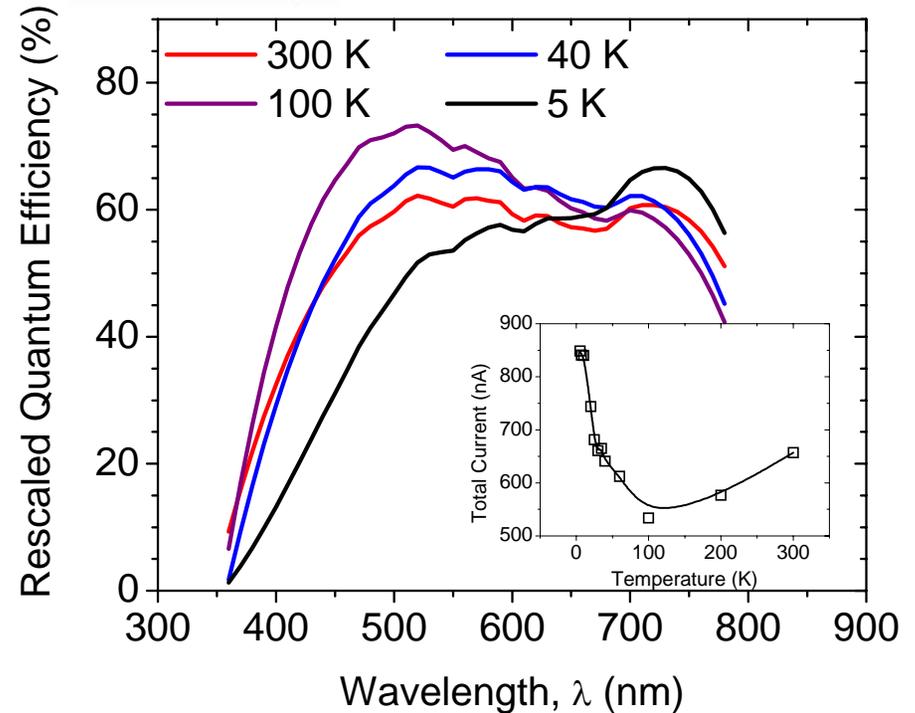
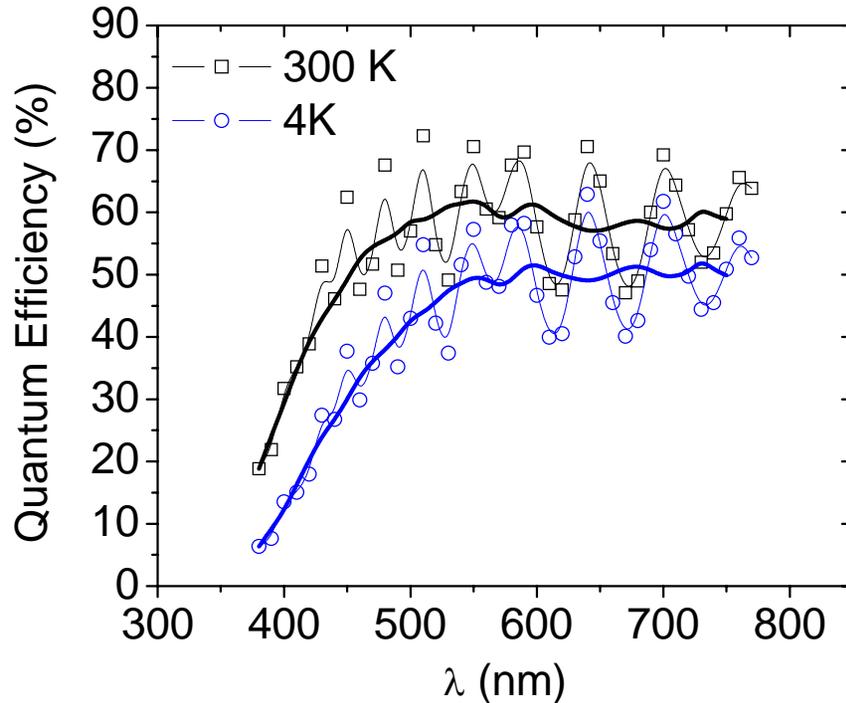
Quantum Efficiency



Open window to cryostat

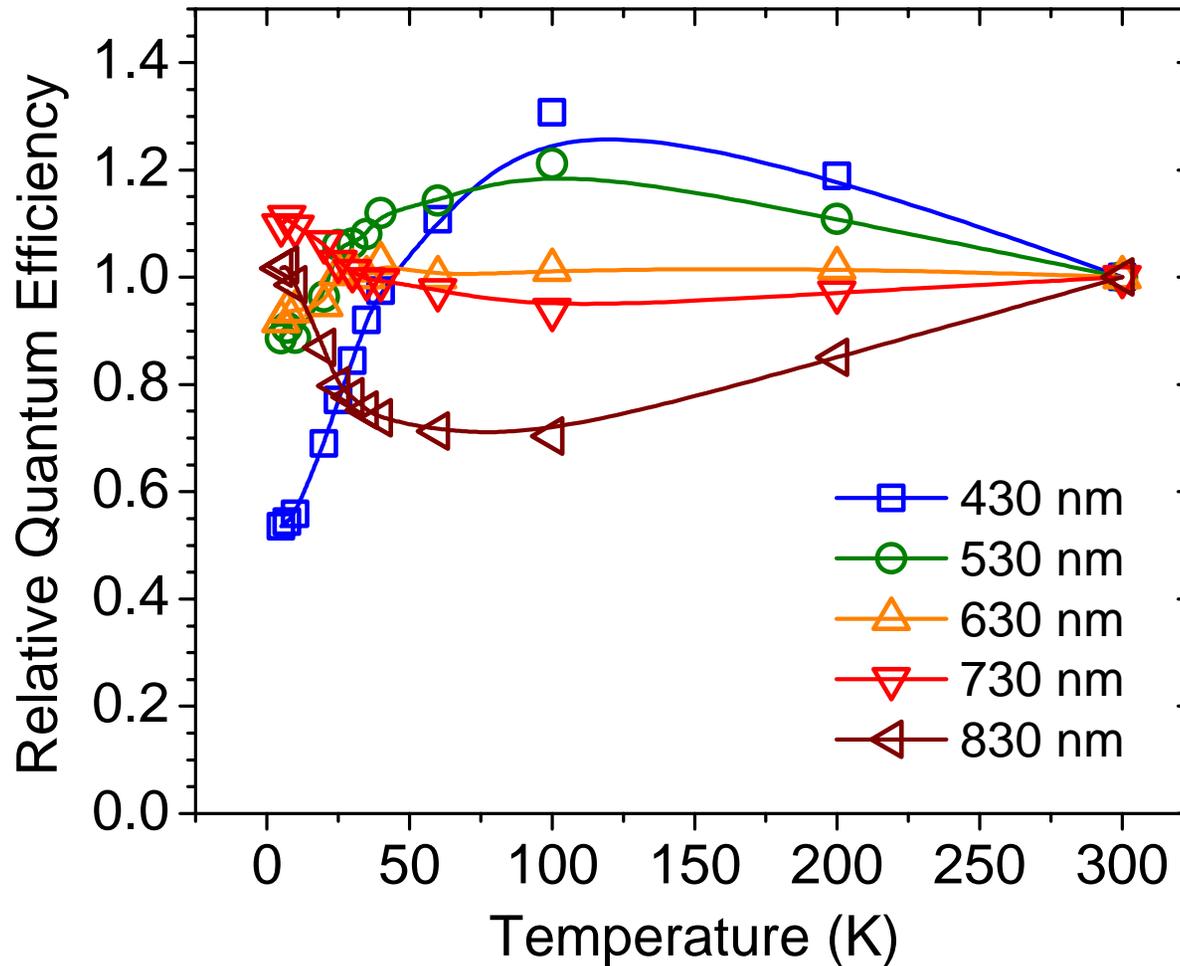


Piped in light using fiber

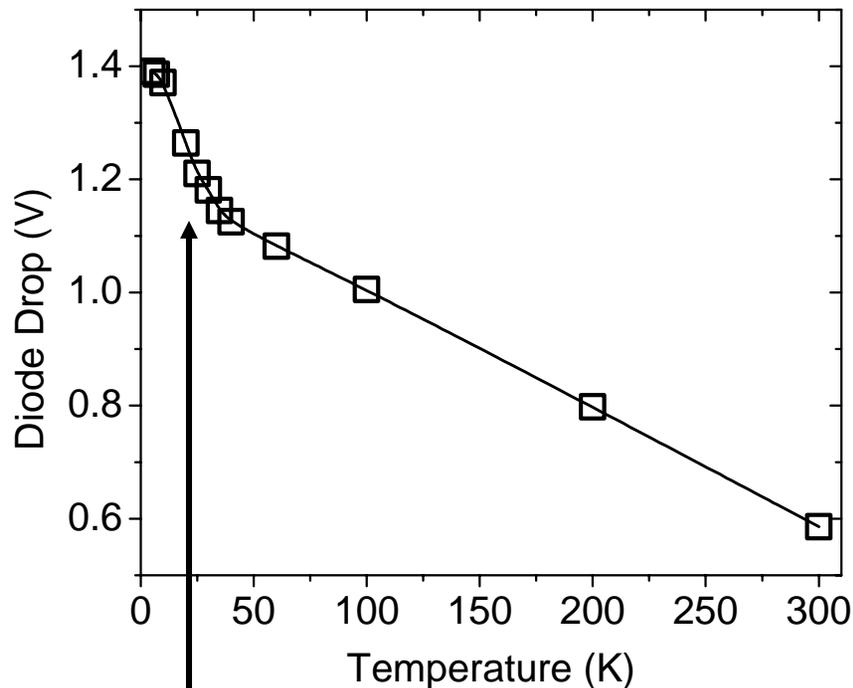


- Device is at 0V
- To measure QE at low temperature, the current at low temperatures is compared to the RT currents.
- Rescaled QE to account for possible changes in light transmission.

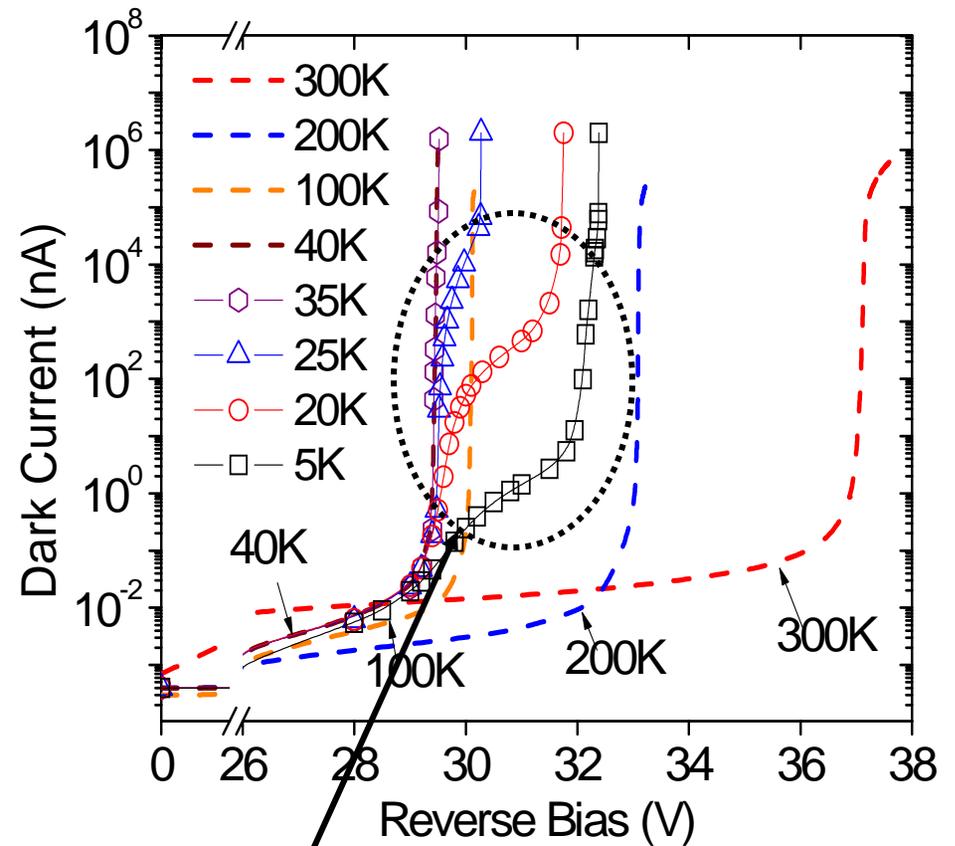
Relative Quantum Efficiency



IV Curves and Diode Drop

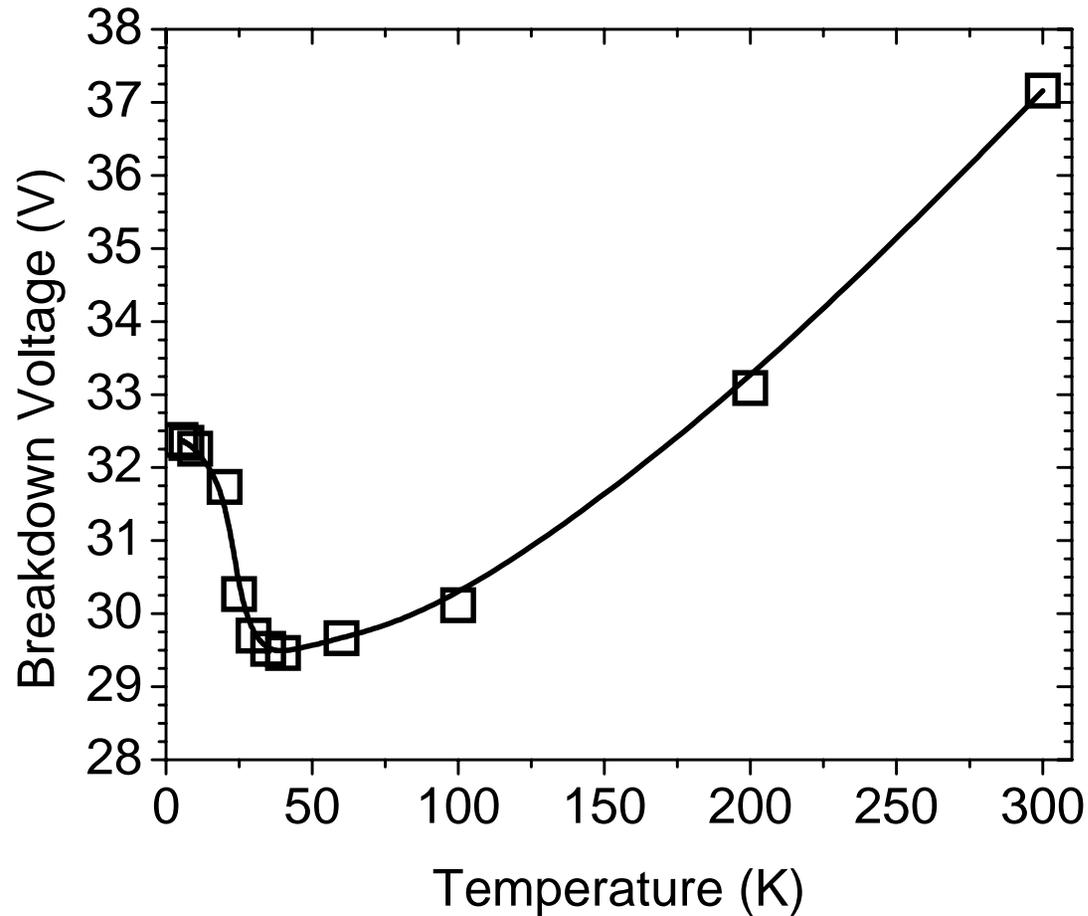


"freeze-out"



Additional Series Resistance Term

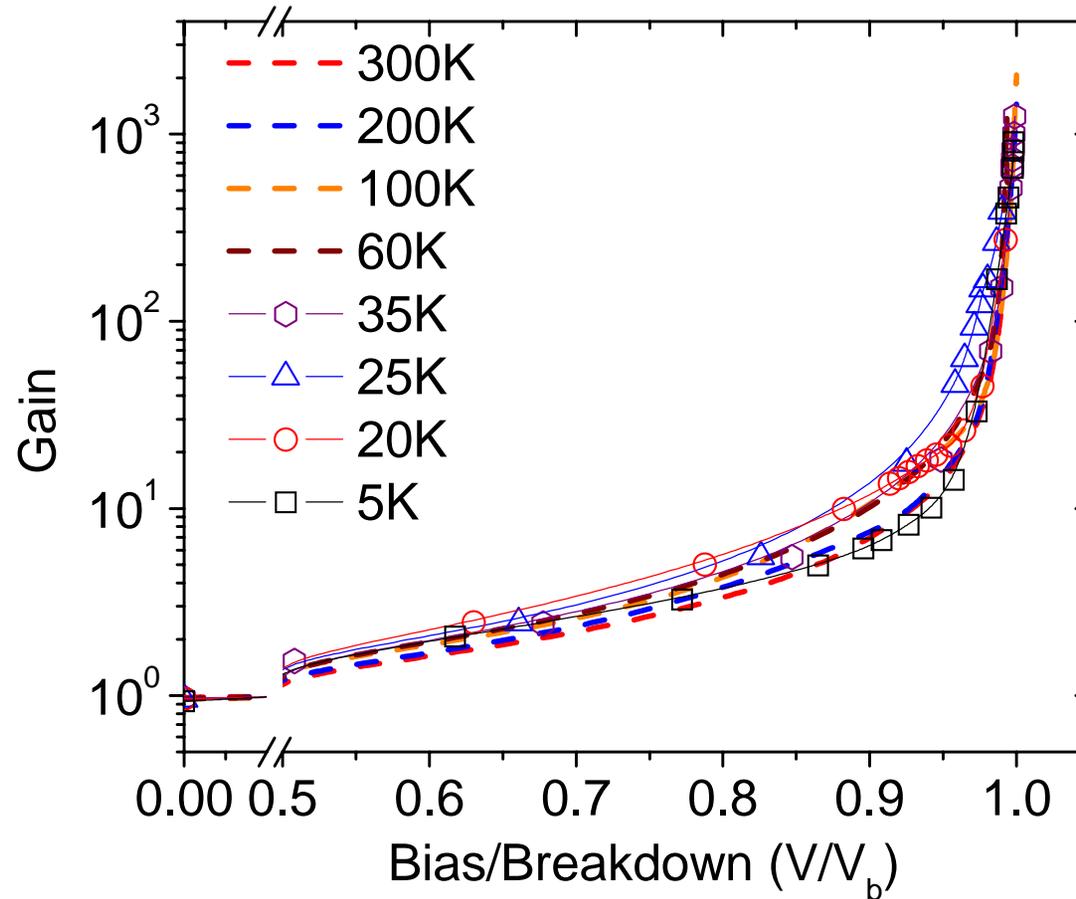
Breakdown



➤ **Strong dependence on temperature.**

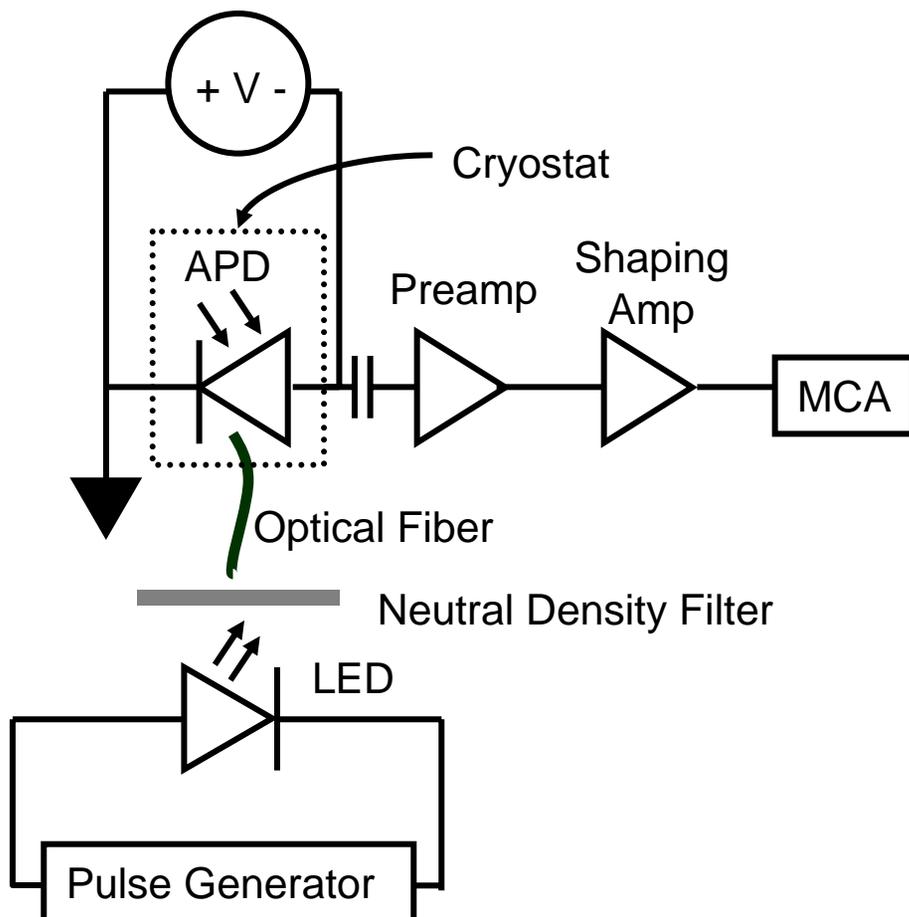
Gain

$$\text{Gain} \propto \frac{1}{1 - \left(\frac{V}{V_b}\right)^n}$$



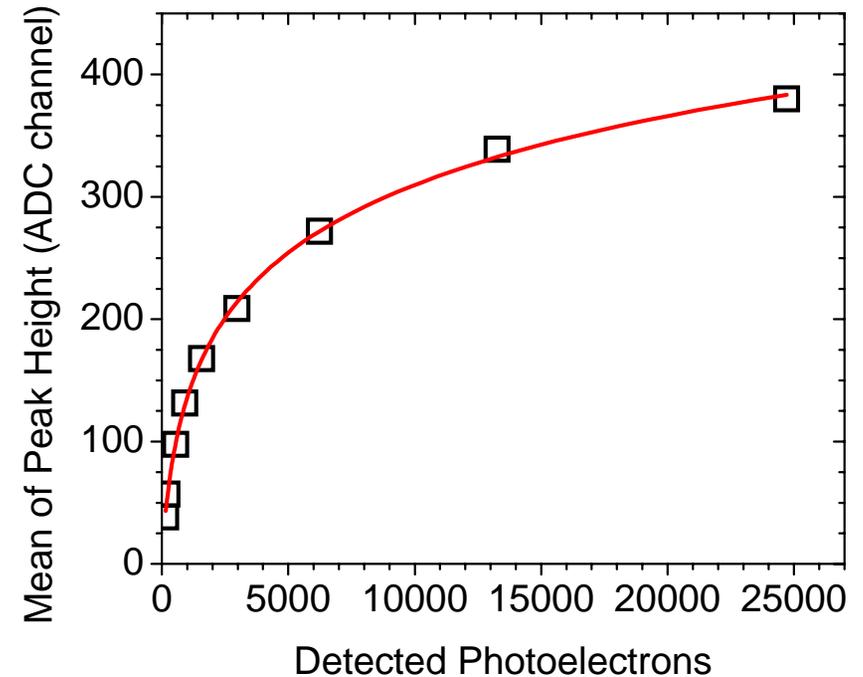
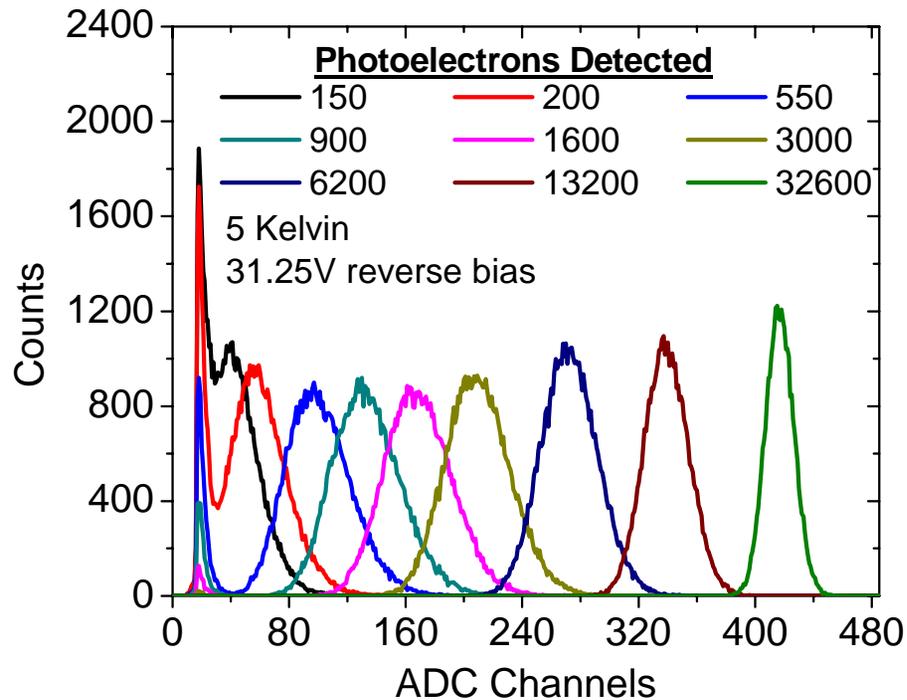
- Measured using 532-nm LED light
- Weak dependence on temperature.

Pulsed Light



- 532-nm LED is driven with a 20-ns pulse.
- Neutral density filters are used to attenuate light intensity.
- Signal coupled to the Amptek CoolFET charge-sensitive preamplifier.
- Used a 20-ns shaping time.
- Fed signal into a Amptek Pocket MCA.

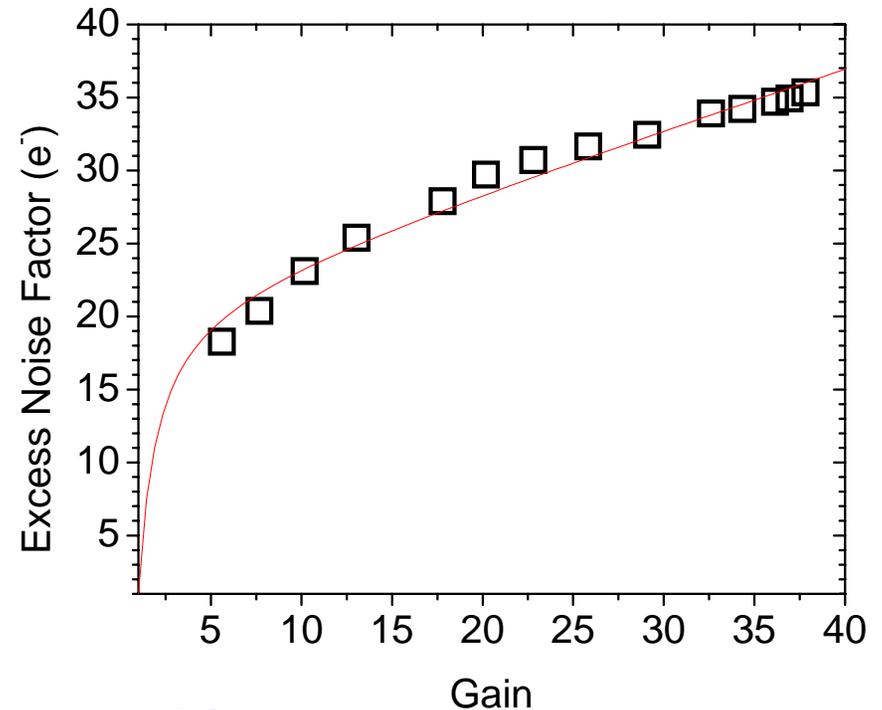
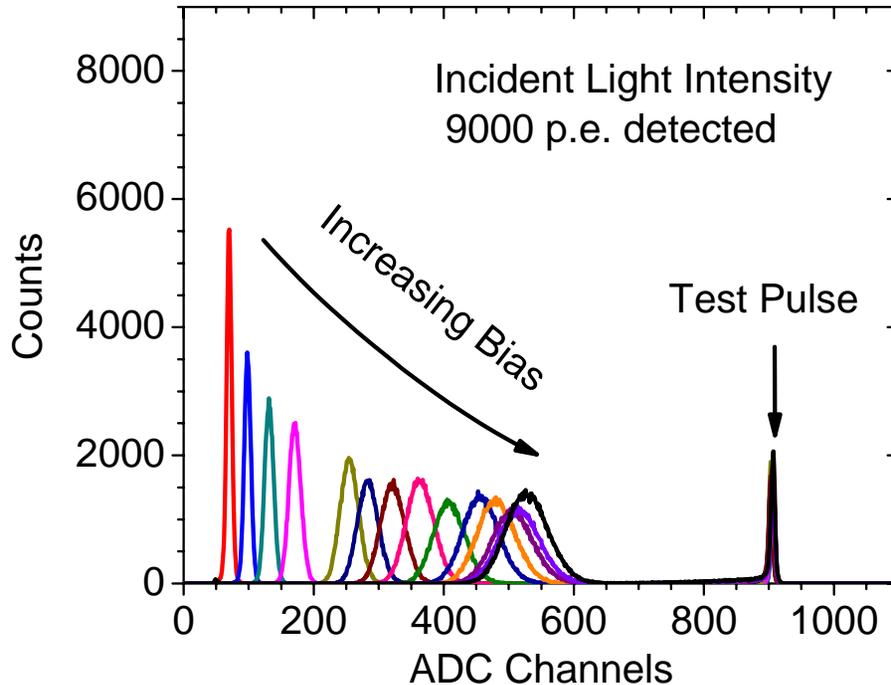
Response



- Temperature = 5 K
- Bias = 31.25 V: Gain ~20
- Changed NDF to vary light intensity.

Excess Noise

$$F = \frac{\sigma_{total}^2}{\sigma_{photons}^2 + \sigma_{dark}^2}$$

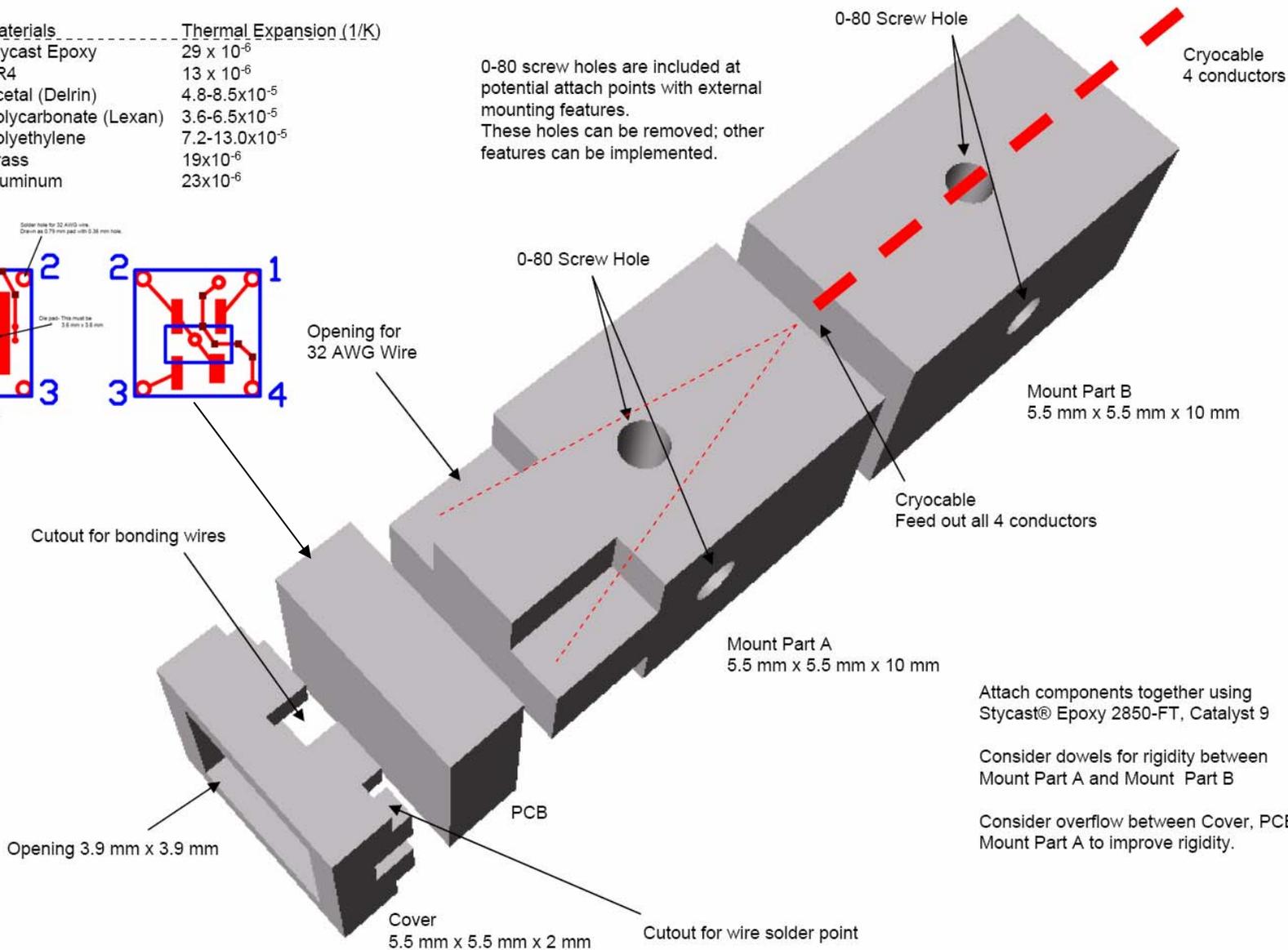
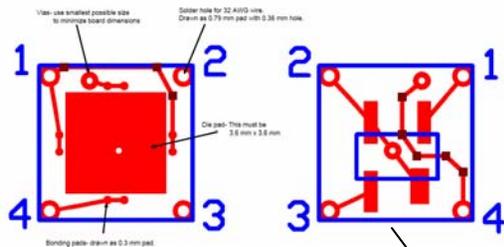


- Set a constant light intensity but vary bias.
- Room temperature excess noise can be explained in terms of the hole to electron ionization ratio, κ , and the gain.
- The dependence shown here has an addition term or an offset.

Readout & Packaging

Materials	Thermal Expansion (1/K)
Stycast Epoxy	29×10^{-6}
FR4	13×10^{-6}
Acetal (Delrin)	$4.8-8.5 \times 10^{-5}$
Polycarbonate (Lexan)	$3.6-6.5 \times 10^{-5}$
Polyethylene	$7.2-13.0 \times 10^{-5}$
Brass	19×10^{-6}
Aluminum	23×10^{-6}

0-80 screw holes are included at potential attach points with external mounting features. These holes can be removed; other features can be implemented.



Attach components together using Stycast® Epoxy 2850-FT, Catalyst 9

Consider dowels for rigidity between Mount Part A and Mount Part B

Consider overflow between Cover, PCB, and Mount Part A to improve rigidity.

Schedule

<u>Task</u>	<u>Percent Complete</u>	<u>To Be Completed</u>
Design Proportional Mode Photodetector Elements	100%	
Simulate Heat Constraints for Target Area	100%	
Develop Ancillary Readout Electronics	100%	
Fabricate CMOS Test Array for Cryogenic Evaluation	100%	
Construct Test Apparatus for Evaluation at Low Temperatures	100%	
Measure Characteristics of Prototype Detectors	100%	
Evaluate Photodetector and Select Optimal Design	100%	
Layout and Design Photodetector System	100%	
Fabricate CMOS Photodetector	100%	
Develop Package for Low Temperature and High B-Field Operation	20%	Dec. 2010
Develop Setup for Testing in the HIFROST Environment	0%	Jan. 2011
Create Robust Coupling Between Target and Photodetector.	20%	Mar. 2011
Evaluate Performance in the HIFROST Environment	0%	May 2011
Provide Complete Instrument with Optimized Readout.	10%	Aug. 2011

End of No-Cost Extension August 2011

Final Remarks

- CMOS Geiger Photodiodes are limited at low temperatures.
- CMOS APDs are a viable photodetector at low temperatures.
- Negligible effects from magnetic fields
 - No drift region
 - avalanche process within the depletion width ~10 um
- Exploring the implementation of a FET coupled directly to the APD for signal to noise improvement.
- Potential low-cost device for scientific experimentation within a operation regime of
 - Temperatures (<100 Kelvin)
 - High Magnetic Fields (>50 Gauss)
 - Compact (Die size of 1.5 mm x 1.5 mm)
 - Low Voltage (<50 V)
 - Solid-state: No vacuum tubes- less sensitive to environment.
 - Can be exposed to ambient light while biased for short periods without adverse effects.
- We have been solicited by scientists regarding this instrument for other low temperature nuclear experiments.

